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501.36931CX1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: IWASAKI, et al

Serial No.: 09/985,904

Filed: November 6, 2001

For: SEMICONDUCTOR DEVICE HAVING LAYERED  
INTERCONNECT STRUCTURE WITH A COPPER OR PLATINUM  
CONDUCTING FILM AND A NEIGHBORING FILM (As Amended)

Group Art Unit: 2813

Examiner: Stephen W. Smoot

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JAN 21 2003  
TECHNOLOGY CENTER 2800

AMENDMENT

Assistant Commissioner for Patents  
Washington, D.C. 20231

January 17, 2003

Sir:

In response to the Office Action mailed October 21, 2002, please amend the  
above-identified application as follows:

IN THE CLAIMS:

Please amend the claims presently in the application as follows:

SUB  
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1. (Amended) A semiconductor device having a layered interconnection  
structure including a copper film overlying a surface of a semiconductor substrate,  
wherein the layered interconnection structure includes the copper film and a  
neighboring film located at at least one of (a) adjacent the copper film and (b) between  
the copper film and the semiconductor substrate, the neighboring film having, as a  
primary constituent element thereof, an element selected from a group consisting of  
rhodium, ruthenium, iridium, osmium and platinum, wherein the neighboring film  
substantially prevents voids due to electromigration of copper.

01/21/2003 YS/SLK 09/985,904-1/2135-1/505501

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